

a surface insulating film formed on a surface of the active regions in the first portion and on the side surfaces and bottom surface lining the interior surface of said at least one trench in the second portion; and

a conductive film formed on the surface insulating film, wherein the surface insulating film is sufficiently thin to function as an electric fuse.

4. (Twice Amended) A semiconductor device comprising:

a semiconductor substrate;

at least a trench, having an interior surface formed by side surfaces and a bottom surface, formed in the semiconductor substrate;

a surface insulating film formed along [a] the side surfaces and bottom surface lining the interior surface of the trench [of] and the semiconductor substrate; and

a conductive film formed on the surface insulating film;

wherein the surface insulating film is sufficiently thin to be broken down for forming an electric fuse.

7. (Amended) The semiconductor device according to claim 6, wherein

a plurality of trenches are formed adjacently in the semiconductor substrate [active region], an etching stopper film is embedded in a selected one of the trenches, and a surface insulating film and a conductive film are formed in other trenches.